

FIELD EFFECT TRANSISTOR, METHOD FOR MANUFACTURING
SAME, DISPLAY ELEMENT, DISPLAY DEVICE, AND SYSTEM
ABSTRACT

A method is provided for manufacturing a
5 field effect transistor that includes a gate
insulating layer and an electrode including a first
conductive film and a second conductive film
successively laminated on a predetermined surface of
the gate insulating layer. The method includes steps
10 of forming an oxide film including element A, which
is an alkaline earth metal, and element B, which is
at least one of Ga, Sc, Y and a lanthanide, as the
gate insulating layer; forming a first conductive
film that dissolves in an organic alkaline solution
15 on the oxide film; forming a second conductive film
on the first conductive film; etching the second
conductive film with an etching solution having a
higher etch rate for the second conductive film as
compared with that for the first conductive film; and
20 etching the first conductive film with the organic
alkaline solution using the second conductive film as
a mask.

Fig. 1